



PATENT
Docket No. 20063/OG03-043

**IN THE UNITED STATES PATENT
AND TRADEMARK OFFICE**

March 2, 2004

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The patents and/or publications listed on the enclosed PTO Form-1449 are submitted pursuant to 37 CFR §§ 1.56, 1.97, and 1.98. Copies of the patents or publications are enclosed.

TIME OF FILING

This information disclosure statement is being filed with the application or within three months of the filing date of the application or date of entry into the national stage of an international application or, to the best of the undersigned's knowledge, before the mailing date of a first Office action on the merits, whichever event occurs last. In accordance with 37 CFR §1.97(b), no certification or fee is required.

METHOD OF PAYMENT

No fee is required.

The Commissioner is authorized to charge any fee deficiency required by this paper, or credit any overpayment, to Deposit Account No. 50-2455. A copy of this paper
is enclosed.

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Respectfully submitted,

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March 2, 2004



Form PTO-1449 (Modified)

U.S. Department of Commerce
Patent and Trademark OfficeAtty. Docket No.
20063/OG03-043Serial No.
10/749,489
INFORMATION DISCLOSURE STATEMENT
(Use several sheets if necessary)
Applicant
Seung Hee JWAFiling Date
December 30,
2003Group Art Unit
Unknown**U.S. PATENT DOCUMENTS**

| *EXAMINER INITIALS | | DOCUMENT NUMBER | ISSUE DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|--------------------|-----|-----------------|-------------------|---|-------|----------|----------------------------|
| | A01 | 6,566,195 | May 20, 2003 | Method and Structure for an Improved Floating Gate Memory Cell | 438 | 257 | February 6, 2002 |
| | A02 | 6,326,263 | December 4, 2001 | Method of Fabricating a Flash Memory Cell | 438 | 257 | August 11, 2000 |
| | A03 | 6,153,494 | November 28, 2000 | Method to Increase the Coupling Ration of Word Line to Floating Gate by Lateral Coupling in Stacked Gate of Flash | 438 | 424 | May 12, 1999 |

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.